CPH3459

Power MOSFET 200V, 3.7Ω, 0.5A, Single N-Channel



Features

- On-resistance R_{DS}(on)1=2.8Ω (typ)
- 4V drive
- Halogen free compliance

- Input Capacitance Ciss=90pF (typ)
- Protection Diode in

Specifications

Absolute Maximum Ratings at $Ta = 25^{\circ}C$

Parameter	Symbol	Conditions	Value	Unit
Drain to Source Voltage	VDSS		200	V
Gate to Source Voltage	VGSS		±20	V
Drain Current (DC)	ID		0.5	А
Drain Current (Pulse)	IDP	PW≤10µs, duty cycle≤1%	2	А
Power Dissipation	PD	When mounted on ceramic substrate (900mm ² ×0.8mm)	1.0	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		–55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

Thermal Resistance Ratings

Parameter	Symbol	Value	Unit
Junction to Ambient	R _{θJA}	125	°C/W
When mounted on ceramic substrate (900mm ² ×0.8mm)			

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

Electrical Characteristics at Ta = 25°C

Deventer	0		Value			11.5
Parameter	Symbol Conditions		min	typ	max	Unit
Drain to Source Breakdown Voltage	V(BR)DSS	I _D =1mA, V _{GS} =0V	200			V
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =200V, V _{GS} =0V			1	μΑ
Gate to Source Leakage Current	IGSS	V _{GS} =±16V, V _{DS} =0V			±10	μΑ
Gate Threshold Voltage	VGS(th)	V _{DS} =10V, I _D =1mA	1.2		2.6	V
Forward Transconductance	9FS	V _{DS} =10V, I _D =0.25A		0.8		S
Static Drain to Source On-State Resistance	R _{DS} (on)1	I _D =0.25A, V _{GS} =10V		2.8	3.7	Ω
	R _{DS} (on)2	I _D =0.25A, V _{GS} =4V		2.9	4.1	Ω

Continued on next page.

ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

Parameter	Questo al			Value		
	Symbol	Conditions	min	Тур	max	Unit
Input Capacitance	Ciss	V _{DS} =20V, f=1MHz		90		pF
Output Capacitance	Coss			10		pF
Reverse Transfer Capacitance	Crss			6		pF
Turn-ON Delay Time	t _d (on)	See specified Test Circuit		4		ns
Rise Time	tr			3.5		ns
Turn-OFF Delay Time	t _d (off)			14		ns
Fall Time	tf			45		ns
Total Gate Charge	Qg	V _{DS} =100V, V _{GS} =10V, I _D =0.5A		2.4		nC
Gate to Source Charge	Qgs			0.3		nC
Gate to Drain "Miller" Charge	Qgd			0.8		nC
Forward Diode Voltage	VSD	IS=0.5A, VGS=0V		0.82	1.2	V

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

Ordering & Package Information

Device	Package	Shipping	note
CPH3459-TL-W	CPH3, SC-59 SOT-23, TO-236	3,000 pcs. / reel	Pb-Free and Halogen Free

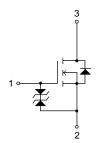
Packing Type:TL

Marking

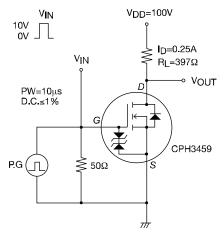


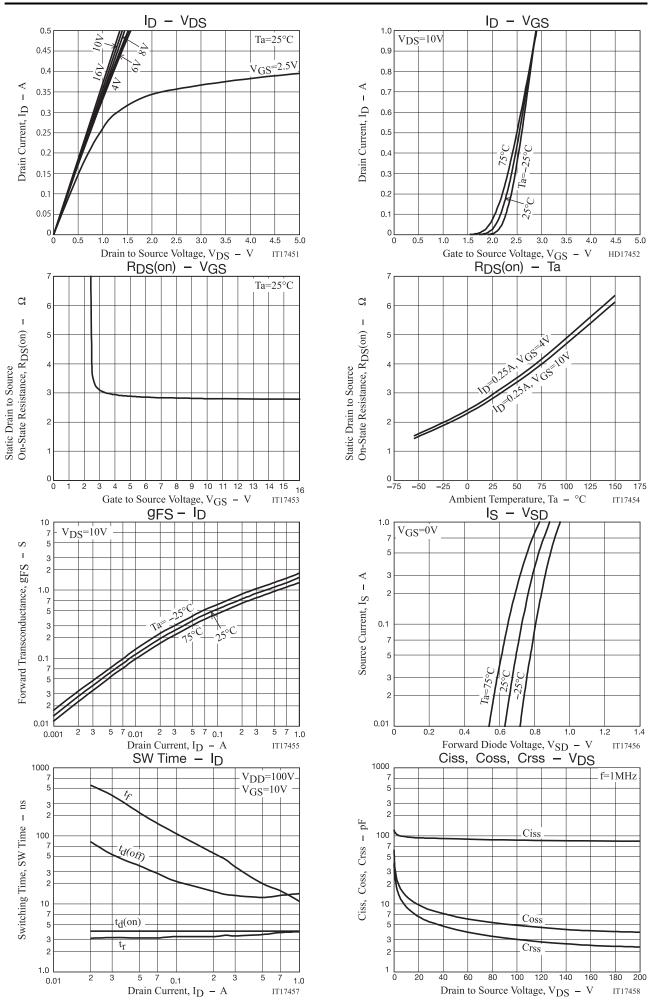


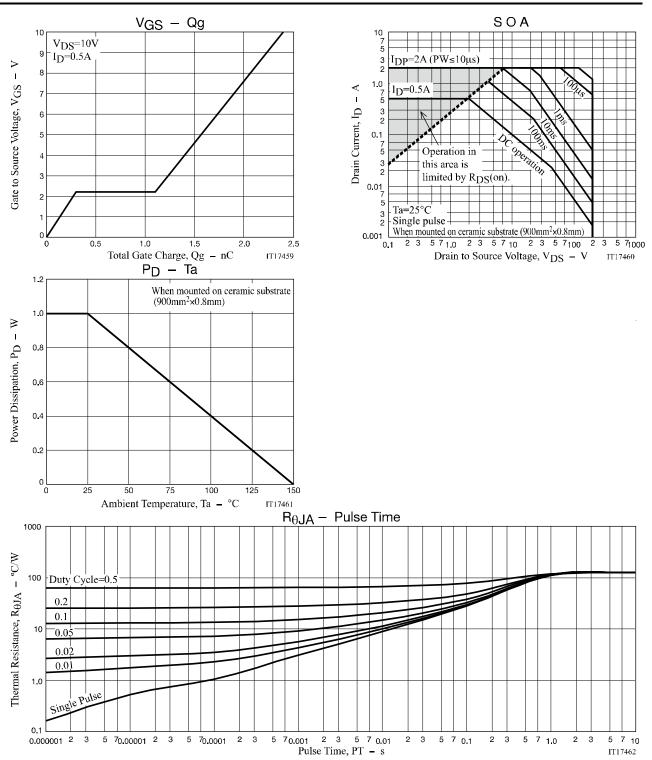
Electrical Connection



Switching Time Test Circuit



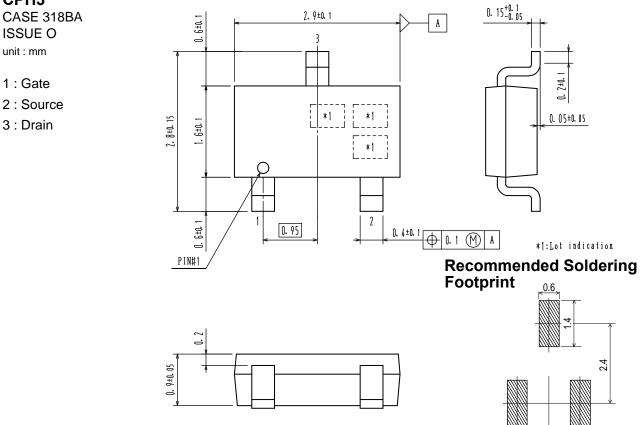




Package Dimensions

CPH3459-TL-W

CPH3



Note on usage : Since the CPH3459 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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